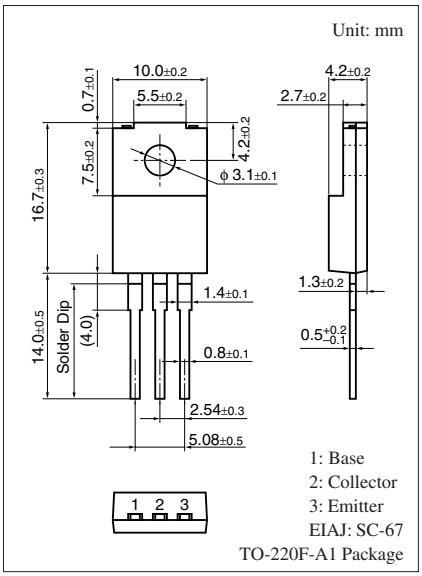
2SB0950 (2SB950), 2SB0950A (2SB950A)

Silicon PNP epitaxial planar type darlington

For power amplification and switching

Complementary to 2SD1276 and 2SD1276A



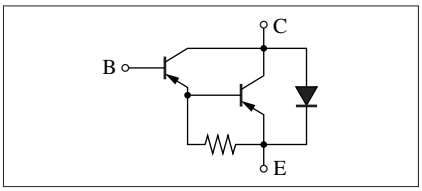
■ Features

- High forward current transfer ratio h_{FE}
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25°C$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SB0950	V_{CBO}	−60	V
	2SB0950A		−80	
Collector-emitter voltage (Base open)	2SB0950	V_{CEO}	−60	V
	2SB0950A		−80	
Emitter-base voltage (Collector open)		V_{EBO}	−5	V
Collector current		I_C	−4	A
Peak collector current		I_{CP}	−8	A
Collector power dissipation	$T_a = 25°C$	P_C	40	W
			2	
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C

Internal Connection



■ Electrical Characteristics $T_C = 25°C \pm 3°C$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SB0950	V_{CEO}	$I_C = -30$ mA, $I_B = 0$	−60			V
	2SB0950A			−80			
Base-emitter voltage		V_{BE}	$V_{CE} = -3$ V, $I_C = -3$ A			−2.5	V
Collector-base cutoff current (Emitter open)	2SB0950	I_{CBO}	$V_{CB} = -60$ V, $I_E = 0$			−200	μA
	2SB0950A		$V_{CB} = -80$ V, $I_E = 0$			−200	
Collector-emitter cutoff current (Base open)	2SB0950	I_{CEO}	$V_{CE} = -30$ V, $I_B = 0$			−500	μA
	2SB0950A		$V_{CE} = -40$ V, $I_B = 0$			−500	
Emitter-base cutoff current (Collector open)		I_{EBO}	$V_{EB} = -5$ V, $I_C = 0$			−2	mA
Forward current transfer ratio		h_{FE1}	$V_{CE} = -3$ V, $I_C = -0.5$ A	1000			—
		h_{FE2} *	$V_{CE} = -3$ V, $I_C = -3$ A	1000		10000	
Collector-emitter saturation voltage		$V_{CE(sat)1}$	$I_C = -3$ A, $I_B = -12$ mA			−2	V
		$V_{CE(sat)2}$	$I_C = -5$ A, $I_B = -20$ mA			−4	V
Transition frequency		f_T	$V_{CE} = -10$ V, $I_C = -0.5$ A, f = 1 MHz		20		MHz
Turn-on time		t_{on}	$I_C = -3$ A, $I_{B1} = -12$ mA, $I_{B2} = 12$ mA		0.3		μs
Storage time		t_{stg}	$V_{CC} = -50$ V		2		μs
Fall time		t_f			0.5		μs

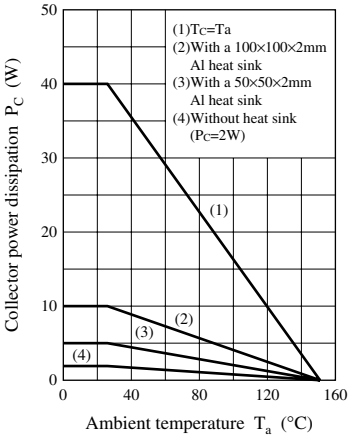
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

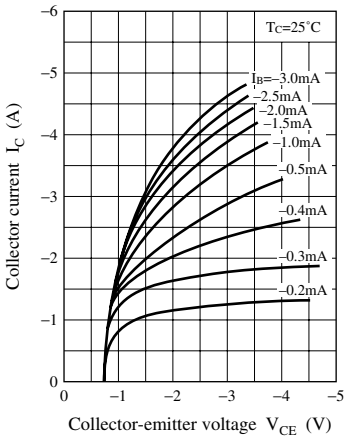
Rank	R	Q	P
h_{FE2}	1000 to 2500	2000 to 5000	4000 to 10000

Note) The part numbers in the parenthesis show conventional part number.

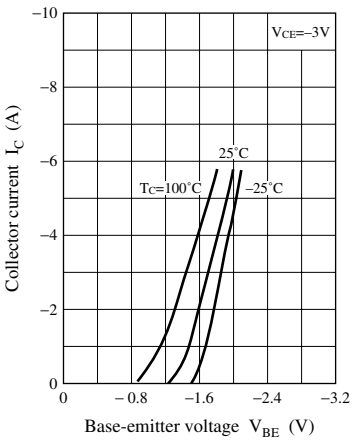
P_C — T_a



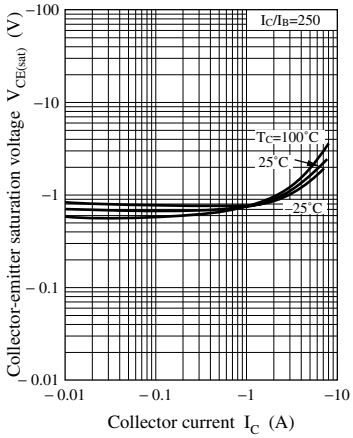
I_C — V_{CE}



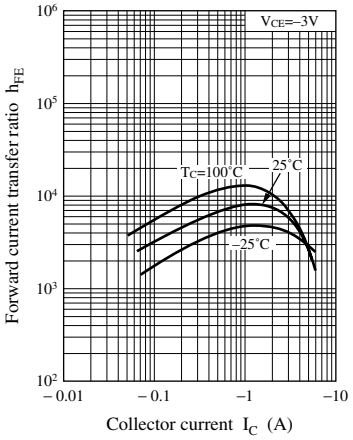
I_C — V_{BE}



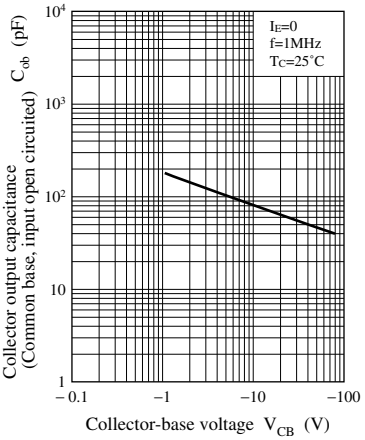
$V_{CE(sat)}$ — I_C



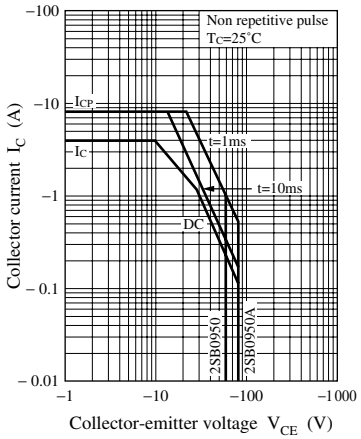
h_{FE} — I_C



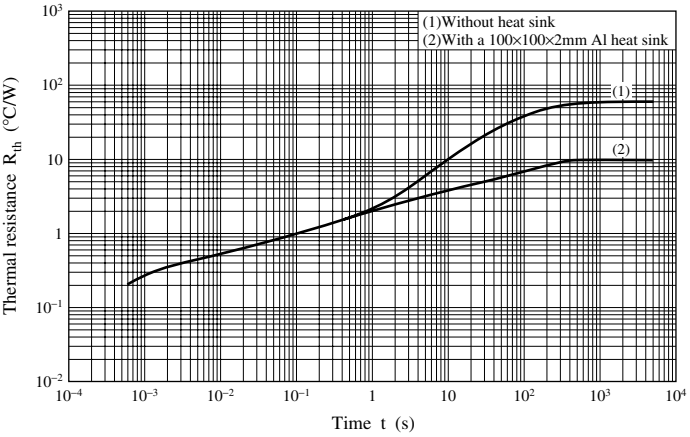
C_{ob} — V_{CB}



Safe operation area



R_{th} — t



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